# Designer's™ Data Sheet

# Insulated Gate Bipolar Transistor N-Channel Enhancement-Mode Silicon Gate

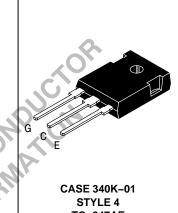
This Insulated Gate Bipolar Transistor (IGBT) uses an advanced termination scheme to provide an enhanced and reliable high voltage–blocking capability. Short circuit rated IGBT's are specifically suited for applications requiring a guaranteed short circuit withstand time. Fast switching characteristics result in efficient operation at high frequencies.

- Industry Standard High Power TO–247 Package with Isolated Mounting Hole
- High Speed E<sub>off</sub>: 160 μJ/A typical at 125°C
- High Short Circuit Capability 10 μs minimum
- Robust High Voltage Termination



Motorola Preferred Device

IGBT IN TO-247 20 A @ 90°C 28 A @ 25°C 1200 VOLTS SHORT CIRCUIT RATED



TO-247AE

OTOROLA

MAXIMUM RATINGS (T <sub>J</sub> =	: 25°C I	unless c	otherwise	e noted)	6	

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V <sub>CES</sub>	1200	Vdc
Collector–Gate Voltage ( $R_{GE} = 1.0 \text{ M}\Omega$ )	V <sub>CGR</sub>	1200	Vdc
Gate-Emitter Voltage — Continuous	V <sub>GE</sub>	±20	Vdc
Collector Current — Continuous @ $T_C = 25^{\circ}C$ — Continuous @ $T_C = 90^{\circ}C$ — Repetitive Pulsed Current (1)	I <sub>C25</sub> I <sub>C90</sub> I <sub>CM</sub>	28 20 56	Adc Apk
Total Power Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	PD	174 1.39	Watts W/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to 150	°C
Short Circuit Withstand Time ( $V_{CC}$ = 720 Vdc, $V_{GE}$ = 15 Vdc, $T_J$ = 125°C, $R_G$ = 20 $\Omega$ )	t <sub>sc</sub>	10	μs
Thermal Resistance — Junction to Case – IGBT — Junction to Ambient	R <sub>θJC</sub> R <sub>θJA</sub>	0.7 35	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 5 seconds	TL	260	°C
Mounting Torque, 6–32 or M3 screw	10 lbf•in (1.13 N•m)		

(1) Pulse width is limited by maximum junction temperature. Repetitive rating.

Designer's Data for "Worst Case" Conditions — The Designer's Data Sheet permits the design of most circuits entirely from the information presented. SOA Limit curves — representing boundaries on device characteristics — are given to facilitate "worst case" design.

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Preferred devices are Motorola recommended choices for future use and best overall value.



## MGW20N120

### **ELECTRICAL CHARACTERISTICS** ( $T_J = 25^{\circ}C$ unless otherwise noted)

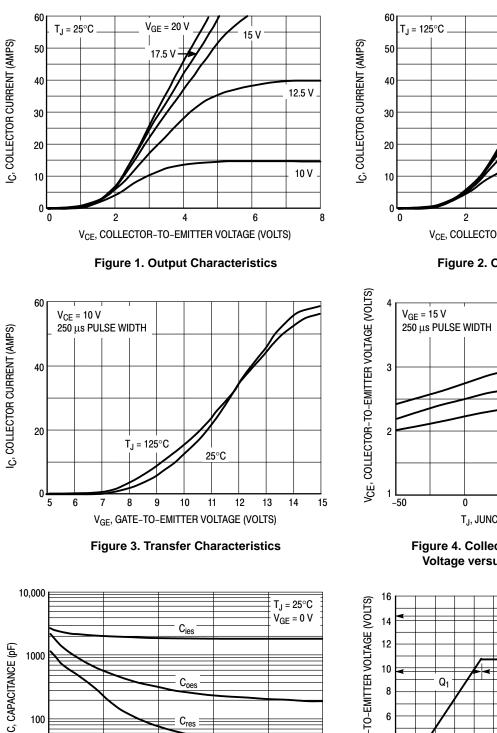
Cha	racteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS						
$\begin{array}{l} \mbox{Collector-to-Emitter Breakdown V} \\ \mbox{(V_{GE}=0 Vdc, I_C=25 \ \mu Adc)} \\ \mbox{Temperature Coefficient (Positive)} \end{array}$	°	V <sub>(BR)CES</sub>	1200 —	 870	_	Vdc mV/°C
Emitter-to-Collector Breakdown Voltage (V <sub>GE</sub> = 0 Vdc, I <sub>EC</sub> = 100 mAdc)		V <sub>(BR)ECS</sub>	25	—	—	Vdc
Zero Gate Voltage Collector Curren ( $V_{CE} = 1200 \text{ Vdc}, V_{GE} = 0 \text{ Vdc}$ ) ( $V_{CE} = 1200 \text{ Vdc}, V_{GE} = 0 \text{ Vdc}$ ,		ICES			100 2500	µAdc
Gate-Body Leakage Current ( $V_{GE} = \pm 20$ Vdc, $V_{CE} = 0$ Vdc)		I <sub>GES</sub>	—	—	250	nAdc
ON CHARACTERISTICS (1)						
$      Collector-to-Emitter On-State Vol(V_{GE} = 15 Vdc, I_C = 10 Adc)(V_{GE} = 15 Vdc, I_C = 10 Adc, T_J =(V_{GE} = 15 Vdc, I_C = 20 Adc)                                   $		V <sub>CE(on)</sub>		2.42 2.36 2.90	3.54  4.99	Vdc
Gate Threshold Voltage ( $V_{CE} = V_{GE}$ , $I_C = 1.0$ mAdc) Threshold Temperature Coefficient	nt (Negative)	V <sub>GE(th)</sub>	4.0	6.0 10	8.0 —	Vdc mV/°C
Forward Transconductance (V <sub>CE</sub> =	10 Vdc, I <sub>C</sub> = 20 Adc)	9 <sub>fe</sub>	—	12	—	Mhos
DYNAMIC CHARACTERISTICS						
Input Capacitance		Cies	—	1860	—	pF
Output Capacitance	(V <sub>CE</sub> = 25 Vdc, V <sub>GE</sub> = 0 Vdc, f = 1.0 MHz)	C <sub>oes</sub>	—	122	—	
Transfer Capacitance	- ,	C <sub>res</sub>	—	29	—	
SWITCHING CHARACTERISTICS (	1)					
Turn-On Delay Time		t <sub>d(on)</sub>	—	88	—	ns
Rise Time	$(V_{CC} = 720 \text{ Vdc}, I_C = 20 \text{ Adc},$	t <sub>r</sub>	—	103	—	
Turn-Off Delay Time	V <sub>GE</sub> = 15 Vdc, L = 300 μH R <sub>G</sub> = 20 Ω)	t <sub>d(off)</sub>	—	190	—	
Fall Time	Energy losses include "tail"	t <sub>f</sub>	—	284	—	
Turn–Off Switching Loss		E <sub>off</sub>	—	1.65	2.75	mJ
Turn–On Delay Time		t <sub>d(on)</sub>	—	83	—	ns
Rise Time	(V <sub>CC</sub> = 720 Vdc, I <sub>C</sub> = 20 Adc,	t <sub>r</sub>	—	107	—	
Turn-Off Delay Time	$\label{eq:GE} \begin{array}{l} V_{GE} = 15 \mbox{ Vdc}, \mbox{ L} = 300  \mu \mbox{H} \\ R_G = 20  \Omega,  T_J = 125^{\circ}\mbox{C} \mbox{)} \\ \mbox{Energy losses include "tail"} \end{array}$	t <sub>d(off)</sub>	—	216	—	
Fall Time		t <sub>f</sub>	—	494	—	1
Turn–Off Switching Loss		E <sub>off</sub>	—	3.19	—	mJ
Gate Charge		QT	—	62	—	nC
(V <sub>CC</sub> = 720 Vdc, I <sub>C</sub> = 20 Adc, V <sub>GE</sub> = 15 Vdc)	Q <sub>1</sub>	—	21	—	]	
		Q <sub>2</sub>	—	25	—	1
NTERNAL PACKAGE INDUCTANO	E					
Internal Emitter Inductance (Measured from the emitter lead	0.25" from package to emitter bond pad)	LE	_	13	_	nH

(1) Pulse Test: Pulse Width  $\leq$  300 µs, Duty Cycle  $\leq$  2%.

15 V

8

## **TYPICAL ELECTRICAL CHARACTERISTICS**



Cres E

V<sub>CE</sub>, COLLECTOR-TO-EMITTER VOLTAGE (VOLTS)

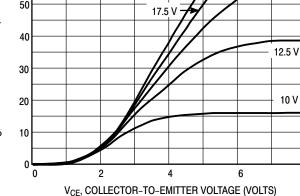
Figure 5. Capacitance Variation

15

20

25

10



V<sub>GE</sub> = 20 V

**Figure 2. Output Characteristics** 

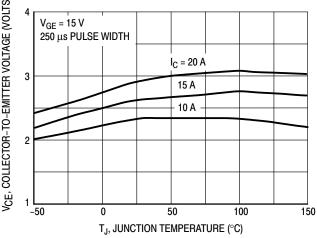


Figure 4. Collector-to-Emitter Saturation **Voltage versus Junction Temperature** 

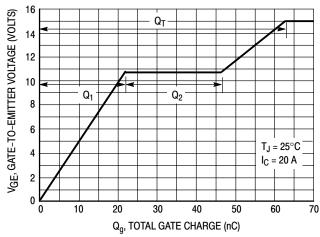


Figure 6. Gate-to-Emitter Voltage versus **Total Charge** 

5

10

0

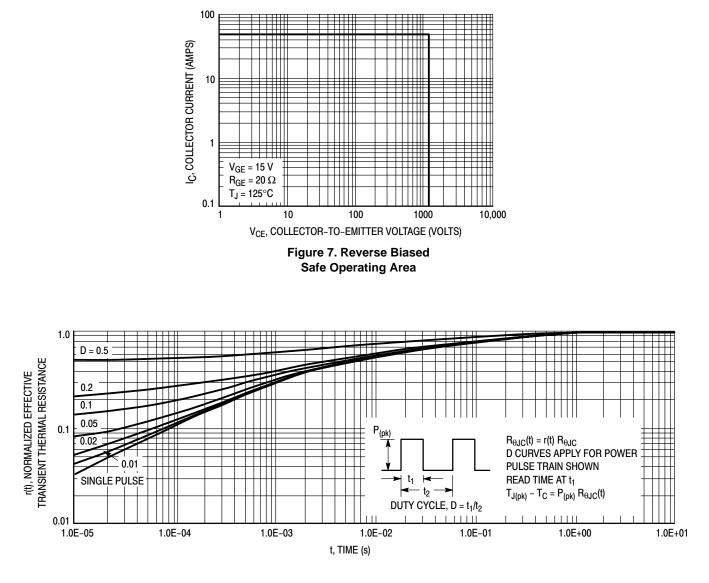
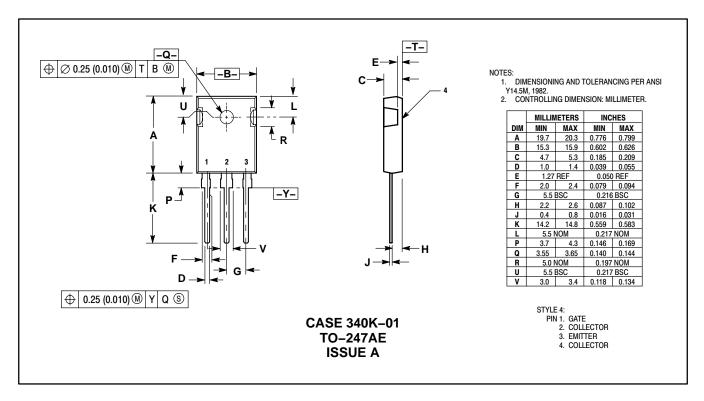


Figure 8. Thermal Response

#### **MGW20N120**

### PACKAGE DIMENSIONS



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